

## CPDZD18VSB-HF

**RoHS Device**  
**Halogen Free**



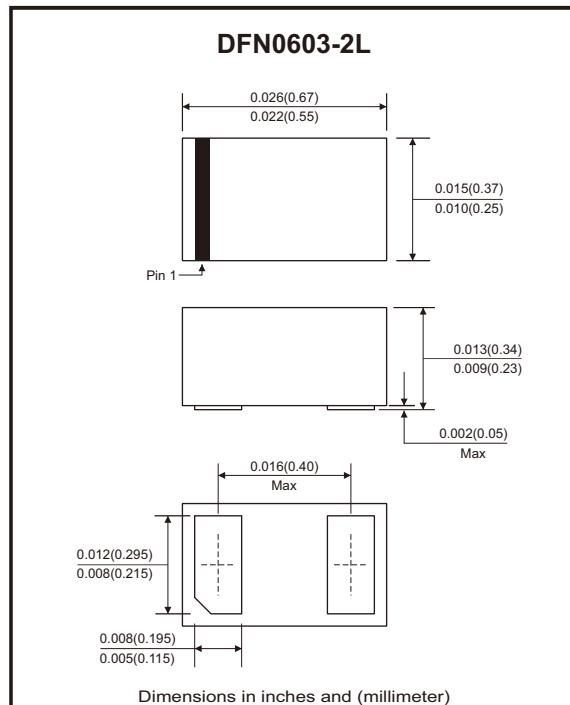
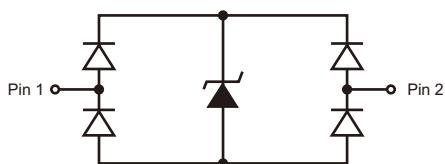
### Features

- Stand-off voltage: 18V (max).
- Transient protection for each line according to IEC 61000-4-2 (ESD):  $\pm 15\text{kV}$  (contact)  
IEC 61000-4-5 (Surge): 4A (8/20 $\mu\text{s}$ )
- Low leakage current.
- Low clamping voltage.
- Solid-state silicon technology.

### Mechanical data

- Case: DFN0603-2L, molded plastic.
- Terminals: Tin plated leads, solderable per J-STD-002 and JESD22-B102.
- Mounting position: Any.

### Circuit Diagram



### Maximum Rating (at $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Value	Unit
Peak pulse power	$T_P = 8/20\mu\text{s}$	$P_{PP}$	40	W
Peak pulse current	$T_P = 8/20\mu\text{s}$	$I_{PP}$	4	A
ESD capability	IEC 61000-4-2(air) IEC 61000-4-2(contact)	ESD	$\pm 15$	kV
Operating junction temperature range		$T_J$	-40 to +125	$^\circ\text{C}$
Storage temperature range		$T_{STG}$	-55 to +150	$^\circ\text{C}$

## Electrical Characteristics (at $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Working peak reverse voltage		$V_{RWM}$			18	V
Reverse leakage current	$V_{RWM} = 18\text{V}$	$I_R$		1	50	nA
Breakdown voltage	$I_T = 1\text{mA}$	$V_{BR}$	18.5			V
Clamping voltage (Note 1)	$TLP = 16\text{A}, T_P = 100\text{ns}$	$V_c$		10		V
Dynamic resistance (Note 1)		$R_{DYN}$		0.25		$\Omega$
Clamping voltage (Note 2)	$V_{ESD} = 8\text{kV}$	$V_c$		10		V
Clamping voltage (Note 3)	$I_{PP} = 1\text{A}, T_P = 8/20\mu\text{s}$	$V_c$		5	6	V
	$I_{PP} = 4\text{A}, T_P = 8/20\mu\text{s}$	$V_c$		9	10	
Junction capacitance	$V_R = 0\text{V}, f = 1\text{MHz}$	$C_J$		0.9	3	pF

Notes: 1. TLP parameter:  $Z_0=50\Omega$ ,  $t_p=100\text{ns}$ ,  $t_r=2\text{ns}$ , averaging window from 60ns to 80ns.  $R_{DYN}$  is calculated from 4A to 16A.

2. Contact discharge mode, according to IEC 61000-4-2.

3. Non-repetitive current pulse, according to IEC 61000-4-5.

# SMD ESD Protection Diode

**Comchip**  
SMD Diode Specialist

## Typical Rating and Characteristic Curves (CPDZD18VSB-HF)

Fig.1 - 8/20 $\mu$ s waveform Per IEC 61000-4-5

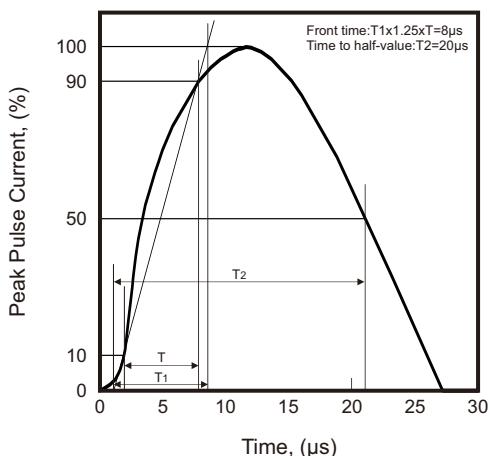


Fig.2 - Contact Discharge Current Waveform  
Per IEC 61000-4-2

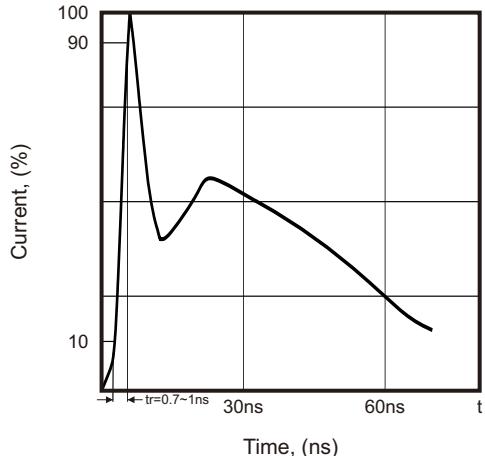


Fig.3 - Clamping Voltage vs.  
Peak Pulse Current

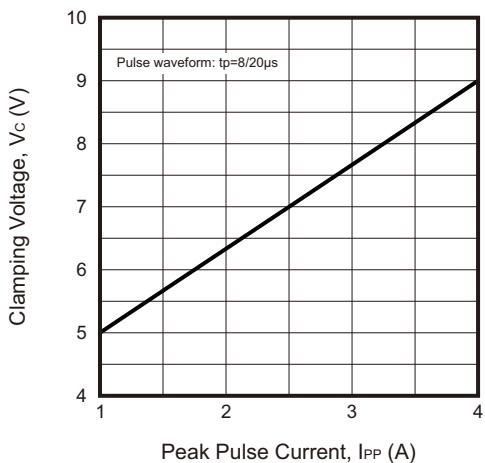


Fig.4 - Typical Capacitance Between  
Terminals Characteristics

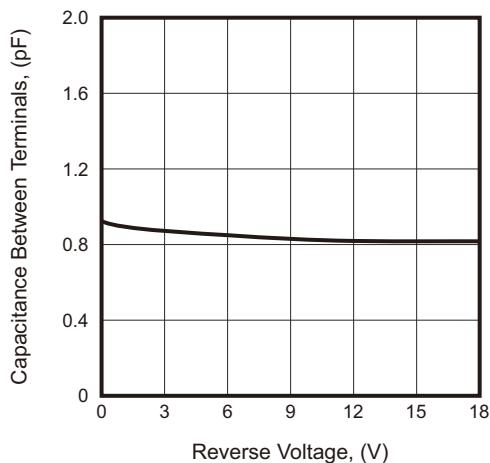


Fig.5 - Non-Repetitive Peak Pulse  
Power vs. Pulse Time

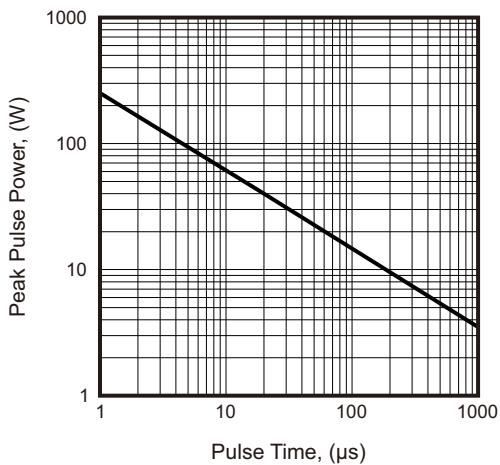
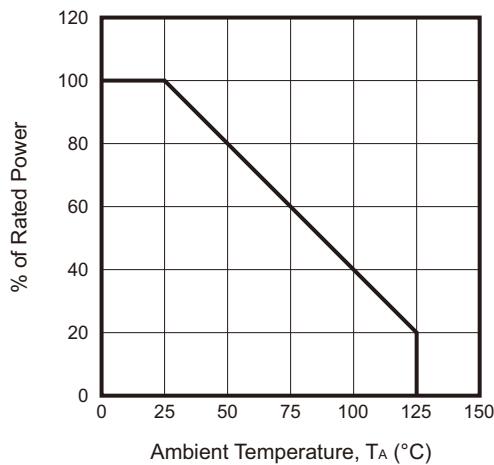


Fig.6 - Power Derating vs.  
Ambient Temperature



# SMD ESD Protection Diode

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## Typical Rating and Characteristic Curves (CPDZD18VSB-HF)

Fig.7 - ESD Clamping  
(+8kV Contact Discharge Per IEC 61000-4-2)

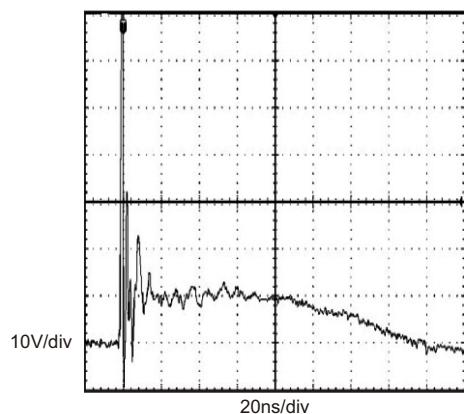


Fig.8 - ESD Clamping  
(-8kV Contact Discharge Per IEC 61000-4-2)

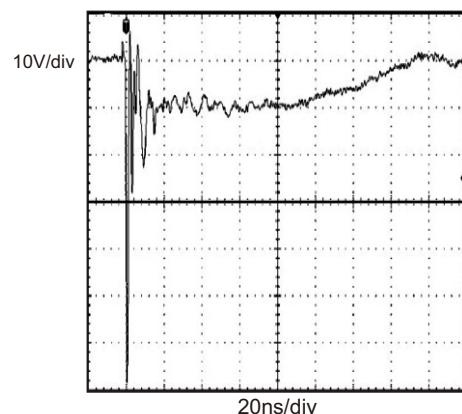
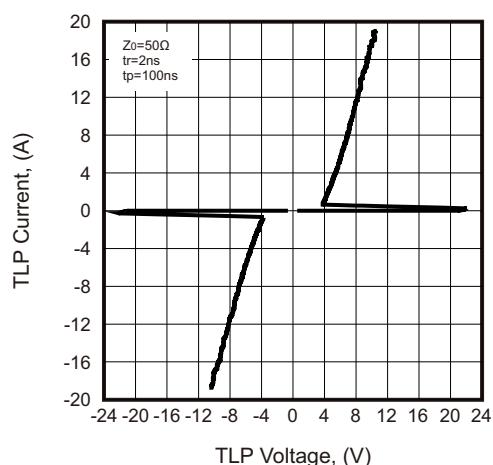
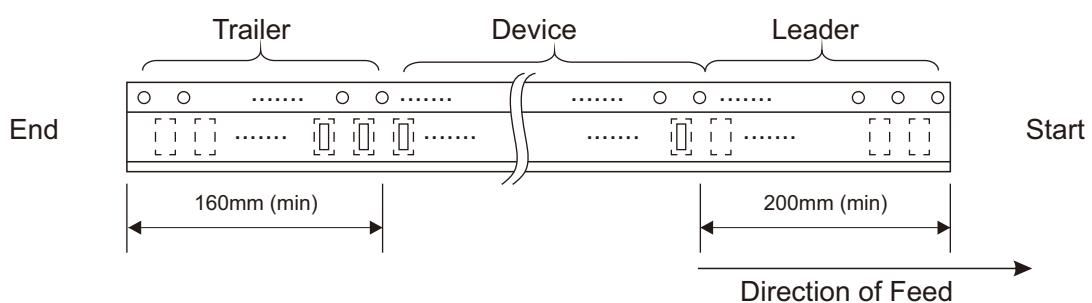
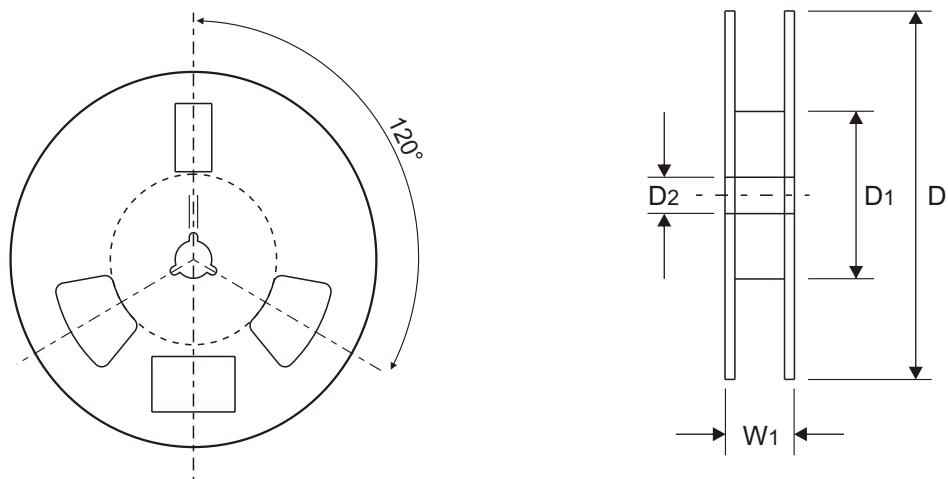
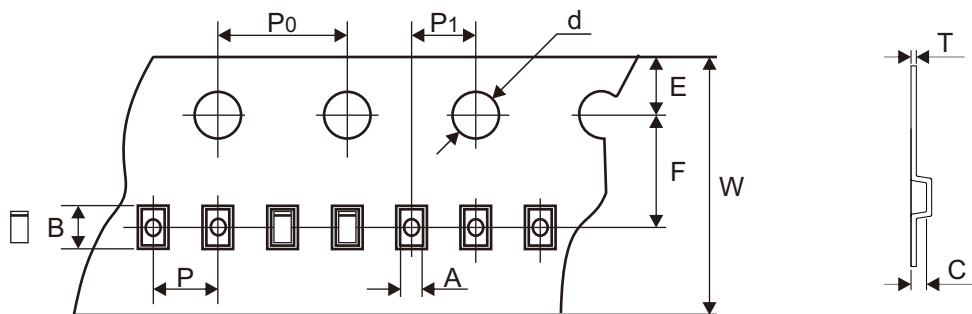


Fig.9 - TLP Measurement



## Reel Taping Specification



DFN0603 -2L	SYMBOL	A	B	C	d	D	D1	D2
	(mm)	$0.45 + 0.05$ $- 0.03$	$0.68 \pm 0.05$	$0.55 \pm 0.05$	$1.50 + 0.10$ $- 0.00$	$178.00 \pm 1.00$	$54.60 \pm 1.00$	$13.30 \pm 1.00$
	(inch)	$0.018 + 0.002$ $- 0.001$	$0.027 \pm 0.002$	$0.022 \pm 0.002$	$0.059 + 0.004$ $- 0.000$	$7.008 \pm 0.039$	$2.150 \pm 0.039$	$0.524 \pm 0.039$

DFN0603 -2L	SYMBOL	E	F	P	P0	P1	T	W	W1
	(mm)	$1.75 \pm 0.05$	$3.50 \pm 0.05$	$2.00 \pm 0.10$	$4.00 \pm 0.10$	$2.00 \pm 0.05$	$0.20 \pm 0.02$	$8.00 + 0.30$ $- 0.10$	$14.40 \pm 1.00$
	(inch)	$0.069 \pm 0.002$	$0.138 \pm 0.002$	$0.079 \pm 0.004$	$0.157 \pm 0.004$	$0.079 \pm 0.002$	$0.008 \pm 0.001$	$0.315 + 0.012$ $- 0.004$	$0.567 \pm 0.039$

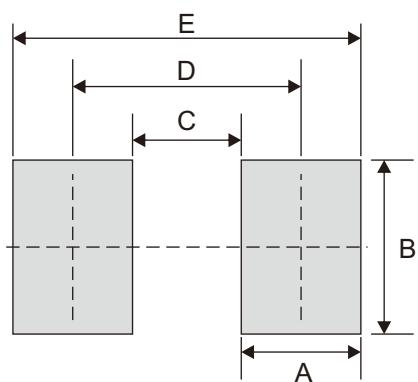
## Marking Code

Part Number	Marking Code
CPDZD18VSB-HF	U8



## Suggested P.C.B. PAD Layout

SIZE	DFN0603-2L	
	(mm)	(inch)
A	0.22	0.009
B	0.32	0.013
C	0.20	0.008
D	0.42	0.017
E	0.64	0.025



## Standard Packaging

Case Type	REEL PACK	
	REEL ( pcs )	Reel Size (inch)
DFN0603-2L	10,000	7